Please amend claims 1-3, 10-11, 27-34 and 42 as follows:

1 (Amended). A semiconductor device comprising:

a first electrode on an organic resin film;

an oxide film of the first electrode in direct contact with at least a portion of a surface of the first electrode; and

a second electrode in direct contact with at least a portion of the oxide film,

wherein a storage capacitor comprises the first electrode and the second electrode with the oxide film interposed therebetween.

2 (Amended). A semiconductor device comprising:

an inorganic film over an organic resin film;

a first electrode on the inorganic film;

an oxide film of the first electrode in direct contact with at least a portion of a surface of the first electrode; and

a second electrode in direct contact with at least a portion of the oxide film,

wherein a storage capacitor comprises the first electrode and the second electrode with the oxide film interposed therebetween.

3 (Amended). A semiconductor device according to claim 2, wherein the inorganic film is formed by sputtering.

10 (Amended). A semiconductor device comprising:

at least a pixel matrix circuit over a substrate;

a storage capacitor in the pixel matrix circuit;

a shielding film provided over an organic resin film;

an oxide film of the shielding film in direct contact with the shielding film; and

a pixel electrode disposed in direct contact with the oxide film,

wherein the storage capacitor comprises the shielding film and the pixel electrode with the oxide film interposed therebetween.

11 (Amended). A semiconductor device comprising:

at least a pixel matrix circuit and a driver circuit over a substrate;

at least an n-channel thin film transistor in the driver circuit;

at least a first lightly doped region in the n-channel thin film transistor;

a first gate electrode in the n-channel thin film transistor;

wherein at least a portion of the first lightly doped region is overlapped with the first gate electrode;

at least a pixel thin film transistor in the pixel matrix circuit;

at least a second lightly doped region in the pixel thin film transistor;

a second gate electrode in the pixel thin film transistor;

wherein the second lightly doped region is not overlapped with the second gate electrode;

at least a storage capacitor in the pixel matrix circuit;

a shielding film over an organic resin film;

an oxide film of the shielding film in direct contact with the shielding film;

a pixel electrode in direct contact with the oxide film;

wherein the storage capacitor comprises the shielding film and the pixel electrode with the oxide film interposed therebetween;

wherein the first lightly doped region comprises an n-type impurity at a higher concentration than the second lightly doped region.

27 (Amended). An electric device using the semiconductor device of claim 1 as a display medium.

28 (Amended). An electric device using the semiconductor device of claim 2 as a display medium.

29 (Amended). An electric device using the semiconductor device of claim 10 as a display medium.

30 (Amended). An electric device using the semiconductor device of claim 11 as a display medium.

31 (Amended). A device according to claim 27,

wherein the electric device is one selected from a group consisting of video camera, digital camera, projector, goggle type display, car navigation system, personal computer and portable information terminal.

32 (Amended). A device according to claim 28,

wherein the electric device is one selected from a group consisting of video camera, digital camera, projector, goggle type display, car navigation system, personal computer and portable information terminal.

33 (Amended). A device according to claim 29,

wherein the electric device is one selected from a group consisting of video camera, digital camera, projector, goggle type display, car navigation system, personal computer and portable information terminal.

cont. A3

34 (Amended). A device according to claim 30,

wherein the electric device is one selected from a group consisting of video camera, digital camera, projector, goggle type display, car navigation system, personal computer and portable information terminal.

---

42 (Amended). A semiconductor device comprising:

A4

at least a pixel matrix circuit over a substrate;

at least a thin film transistor in the pixel matrix circuit;

at least a pixel electrode electrically connected to the thin film transistor;

a first color filter over the pixel matrix circuit;

a second color filter over the pixel matrix circuit;

a third color filter over the pixel circuit,

wherein each of the first, second and third color filters is formed between the thin film transistor and the pixel electrode;

wherein each of the first second and third color filters act as a flattening film;

cont. an organic resin film over each of the first, second and third color films;

A4 a storage capacitor in the pixel matrix circuit, said storage capacitor comprising:

an electrode on the organic resin film;

an oxide film of the electrode in direct contact with the electrode;

the pixel electrode in direct contact with the oxide film.

Please add new claims 43-45.

43 (New). A device according to claim 42,

wherein the first, second and third color filters are arranged in a stripe shape color matrix or a mosaic shape color matrix.

A5

44 (New). A device according to claim 42,

wherein the semiconductor device is a transmission type display device.